

## **AMENDMENT TO SPECIFICATION**

### **IN THE SPECIFICATION:**

A marked-up copy of the changes to selected paragraph(s) is provided below. Please enter these changes to the specification in the record.

Please replace paragraph [0017] with the following paragraph:

[0017] Referring to FIG. 1, an exemplary initial structure employed in the invention is shown. Specifically, the exemplary initial structure is comprised of an SOI substrate 105 having a patterned gate stack region 110 formed on the surface thereof. The SOI substrate 105 may include a buried oxide layer ~~125~~135 sandwiched between a top Si-containing layer 130 and a bottom Si-containing layer 140. The top Si-containing layer 130 is an area upon which devices may be formed. The Si-containing layer 130 may be comprised of various semiconducting materials that include silicon, such as Si, SiGe, SiC, SiGeC, Si/Si, or Si/SiGe.

Please replace paragraph [0025] with the following paragraph:

[0025] Silicon layers 155 and 170 may be formed on the SiGe layers 150 and 165 of the raised source and drain regions 160 and 175, respectively, using a conventional selective epitaxial silicon formation technique. For example, molecular beam epitaxy (MBE) may be used to selectively grow device quality silicon. Because Si has a smaller lattice constant (i.e., atom spacing) than Ge, when Si 155 and 170 is grown on the SiGe layer 160 and 165, the Si 155 and 170 is strained in tension. A suitable thickness for the strained Si layers 155 and 170 is below the critical thickness, which is the maximum thickness that strained Si can grow on the SiGe-SiGe layers 150 and 165 without forming defects in the crystal structure (e.g., dislocations). By way of example but not limitation, the strained Si layer 155 may be approximately 5 to 100 nm thick.

Please replace paragraph [0031] with the following paragraph:

[0031] The spacers 505 and 525 may be formed along the Si coated SiGe sidewalls of the raised drain in a conventional manner, such as by oxide deposition, patterning and etching using processes known in the art. After formation of the spacers, an additional selective epitaxial growth step may be performed to complete formation of the raised drain. The oxide spacers 505 and 525 will prevent further formation of Si along the sidewalls during the additional selective epitaxial growth step. After completing the ~~sadditional~~additional selective epitaxial growth step, the oxide spacers may be removed, such as by dry etching.